

8 TO 3 LINE PRIORITY ENCODER

- HIGH SPEED
 - $t_{PD} = 15 \text{ ns} (TYP.) AT V_{CC} = 5 \text{ V}$
- LOW POWER DISSIPATION $I_{CC} = 4 \mu A \text{ (MAX.)} \text{ AT } T_A = 25 \text{ °C}$
- HIGH NOISE IMMUNITY

 VNIH = VNIL = 28 % VCC (MIN.)
- OUTPUT DRIVE CAPABILITY 10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE | I_{OH} | = I_{OL} = 4 mA (MIN.)
- BALANCED PROPAGATION DELAYS tplh = tphl
- WIDE OPERATING VOLTAGE RANGE Vcc (OPR) = 2 V TO 6 V
- PIN AND FUNCTION COMPATIBLE WITH 54/74LS148

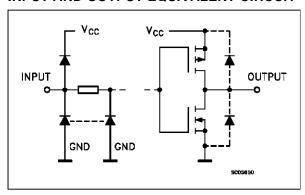
DESCRIPTION

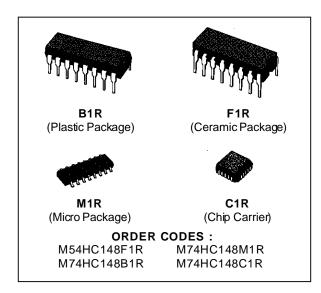
The M54/74HC148 is a high speed CMOS 8-TO-3 LINE PRIORITY ENCODER fabricated in silicon gate C²MOS technology.

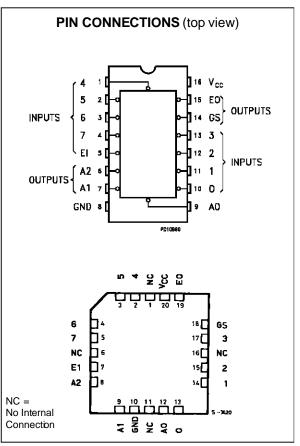
It has the same high speed performance for LSTTL combined with true CMOS low power consumption. The M54/74HC148 encodes eight data lines to three-line (4-2-1) binary (octal). Cascading circuitry (enable input EI and enable output EO) has been provided to allow octal expansion without the need for external circuitry. Data inputs are active at the low logic level.

All inputs are equipped with protection circuits against static discharge and transient excess voltage.

INPUT AND OUTPUT EQUIVALENT CIRCUIT







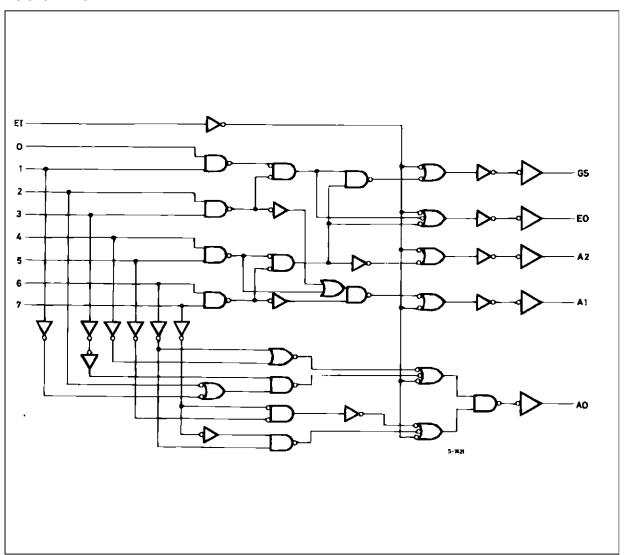
October 1992 1/11

TRUTH TABLE

				INPUTS					OUTPUTS				
E1	0	1	2	3	4	5	6	7	A2	A 1	A0	GS	E0
Н	Х	X	X	Х	X	Х	Х	X	Н	Н	Н	Н	Н
L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	L
L	Х	Х	Х	Х	X	Х	Х	L	L	L	L	L	Η
L	Х	Х	Х	Х	X	Х	L	Н	L	L	Н	L	Н
L	Х	X	Х	Х	Х	L	Н	Н	L	Н	L	L	Η
L	Х	X	Х	Х	L	Н	Н	Н	L	Н	Н	L	Н
L	Х	X	Х	L	Н	Н	Н	Н	Н	L	L	L	Н
L	Х	Х	L	Н	Н	Н	Н	Н	Н	LL	Н	L	Н
L	Х	L	Н	Н	Н	Н	Н	Н	Н	Н	L	L	Η
L	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	L	Н

X: Don't Care

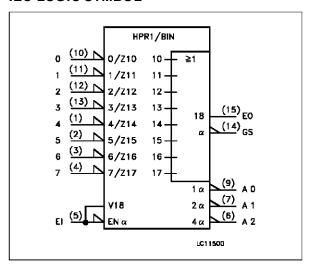
LOGIC DIAGRAM



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION			
9, 7, 6	A0 to A2	Data Outputs			
11, 12, 13, 1, 2, 3, 4, 10	0 to 7	Data Inputs			
15	EO	Enable Output			
5	El	Enable Input			
14	GS	Priority Flag Output			
8	GND	Ground (0V)			
16	Vcc	Positive Supply Voltage			

IEC LOGIC SYMBOL



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	-0.5 to +7	V
VI	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
lok	DC Output Diode Current	± 20	mA
Ιο	DC Output Source Sink Current Per Output Pin	± 25	mA
Icc or Ignd	DC Vcc or Ground Current	± 50	mA
P_{D}	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied. (*) 500 mW: \equiv 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Value	Unit
Vcc	Supply Voltage		2 to 6	V
V_{I}	Input Voltage		0 to V _{CC}	V
Vo	Output Voltage		0 to V _{CC}	V
T_op	Operating Temperature: M54HC Series M74HC Series		-55 to +125 -40 to +85	°C °C
t _r , t _f	Input Rise and Fall Time	V _{CC} = 2 V	0 to 1000	ns
		$V_{CC} = 4.5 \text{ V}$	0 to 500	
		Vcc = 6 V	0 to 400	



DC SPECIFICATIONS

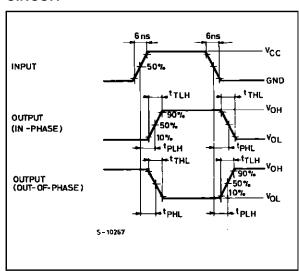
		Test Conditions						Value				
Symbol	Parameter	Vcc			$T_A = 25$ °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		Unit
		(V)			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input	2.0			1.5			1.5		1.5		
	Voltage	4.5			3.15			3.15		3.15		V
		6.0			4.2			4.2		4.2		
V _{IL}	Low Level Input	2.0					0.5		0.5		0.5	
	Voltage	4.5					1.35		1.35		1.35	V
		6.0					1.8		1.8		1.8	
Vон	High Level Output Voltage	2.0	Vı =		1.9	2.0		1.9		1.9		
		4.5	VI –	la=-'2() \	4.4	4.5		4.4		4.4		\ ,,
		6.0	or		5.9	6.0		5.9		5.9		V
		4.5	V _{IL} I _O =-4.0 mA	4.18	4.31		4.13		4.10			
		6.0		lo=-5.2 mA	5.68	5.8		5.63		5.60		
V_{OL}	Low Level Output	2.0	V _I =			0.0	0.1		0.1		0.1	
	Voltage	4.5	VIH	I _O = 20 μA		0.0	0.1		0.1		0.1	
		6.0	or			0.0	0.1		0.1		0.1	V
		4.5	VIL	I _O = 4.0 mA		0.17	0.26		0.33		0.40	
		6.0		I _O = 5.2 mA		0.18	0.26		0.33		0.40	
lı	Input Leakage Current	6.0	V _I = '	V _{CC} or GND			±0.1		±1		±1	μА
Icc	Quiescent Supply Current	6.0	V _I = '	V _{CC} or GND			4		40		80	μА

AC ELECTRICAL CHARACTERISTICS	$(C_L = 50)$	pF, Input $t_r = t_f = 6$ ns)
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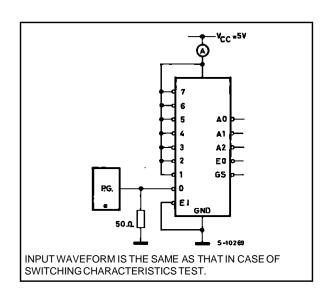
		Te	st Conditions	Value							
Symbol	Parameter	V _{CC}			T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC	
		(۷)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t _{TLH}	Output Transition	2.0			30	75		95		110	
t _{THL}	t _{THL} Time	4.5			8	15		19		22	ns
	6.0			7	13		16		19		
t _{PLH}	Propagation	2.0			60	150		190		225	
t _{PHL}	Delay Time	4.5			19	30		38		45	ns
(In - A0, A1, A2)	6.0			16	26		32		38		
t _{PLH} Propagation	2.0			60	150		190		225		
t _{PHL}	t _{PHL} Delay Time (In - EO, GS)	4.5			19	30		38		45	ns
		6.0			16	26		32		38	
t _{PLH}	Propagation	2.0			40	115		145		175	
t _{PHL}	Delay Time	4.5			14	23		29		35	ns
	(EI - EO)	6.0			12	20		25		30	
t _{PLH}	Propagation	2.0			40	115		145		175	
t _{PHL}	Delay Time	4.5			14	23		29		35	ns
	(EI - GS)	6.0			12	20		25		30	
t _{PLH}	Propagation	2.0			40	115		145		175	
t _{PHL}		4.5			14	23		29		35	ns
	(EI - A0, A1, A2)	6.0			12	20		25		30	
C _{IN}	Input Capacitance				5	10		10		10	рF
C _{PD} (*)	Power Dissipation Capacitance				60						pF

^(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. Icc(opr) = C_{PD} • V_{CC} • f_{IN} + I_{CC}

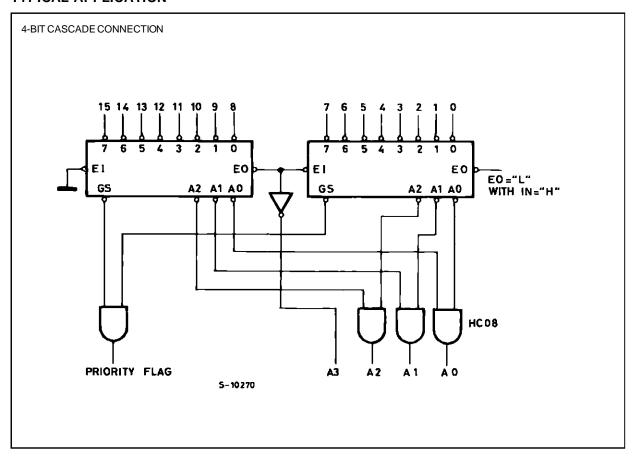
SWITCHING CHARACTERISTICS TEST CIRCUIT



TEST CIRCUIT ICC (Opr.)

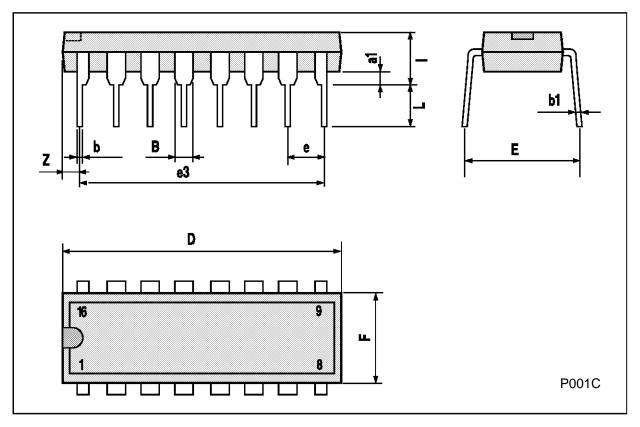


TYPICAL APPLICATION



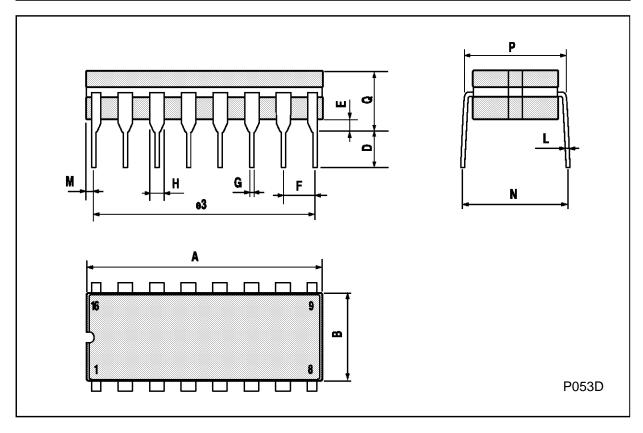
Plastic DIP16 (0.25) MECHANICAL DATA

DIM.		mm		inch				
Dini.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	0.77		1.65	0.030		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
E		8.5			0.335			
е		2.54			0.100			
e3		17.78			0.700			
F			7.1			0.280		
I			5.1			0.201		
L		3.3			0.130			
Z			1.27			0.050		



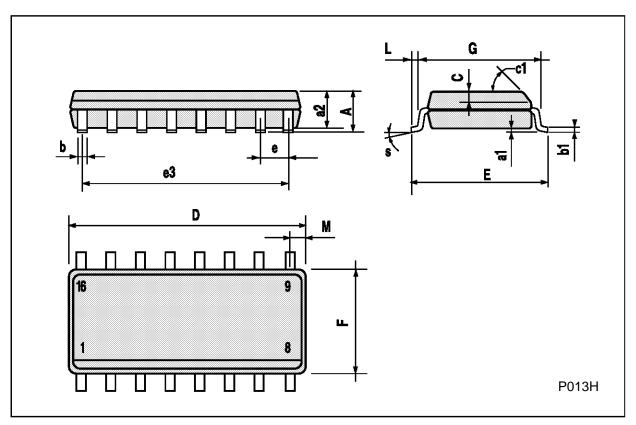
Ceramic DIP16/1 MECHANICAL DATA

DIM.		mm		inch				
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
А			20			0.787		
В			7			0.276		
D		3.3			0.130			
Е	0.38			0.015				
e3		17.78			0.700			
F	2.29		2.79	0.090		0.110		
G	0.4		0.55	0.016		0.022		
Н	1.17		1.52	0.046		0.060		
L	0.22		0.31	0.009		0.012		
М	0.51		1.27	0.020		0.050		
N			10.3			0.406		
Р	7.8		8.05	0.307		0.317		
Q			5.08			0.200		



SO16 (Narrow) MECHANICAL DATA

DIM.		mm		inch				
DIWI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
А			1.75			0.068		
a1	0.1		0.2	0.004		0.007		
a2			1.65			0.064		
b	0.35		0.46	0.013		0.018		
b1	0.19		0.25	0.007		0.010		
С		0.5			0.019			
c1			45° ((typ.)				
D	9.8		10	0.385		0.393		
E	5.8		6.2	0.228		0.244		
е		1.27			0.050			
e3		8.89			0.350			
F	3.8		4.0	0.149		0.157		
G	4.6		5.3	0.181		0.208		
L	0.5		1.27	0.019		0.050		
М			0.62			0.024		
S			8° (n	nax.)				



PLCC20 MECHANICAL DATA

DIM.		mm		inch				
Diiii.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
А	9.78		10.03	0.385		0.395		
В	8.89		9.04	0.350		0.356		
D	4.2		4.57	0.165		0.180		
d1		2.54			0.100			
d2		0.56			0.022			
E	7.37		8.38	0.290		0.330		
е		1.27			0.050			
e3		5.08			0.200			
F		0.38			0.015			
G			0.101			0.004		
М		1.27			0.050			
M1		1.14			0.045			



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